

International Rectifier IRFK3D250, IRFK3F250

Isolated Base Power HEX-pak™ Assembly - Half Bridge Configuration

- High Current Capability.
- UL recognised E78996.
- Electrically Isolated Base Plate.
- Easy Assembly into Equipment.

Description

The HEX-pak™ utilises the well-proven HEXFET™ die, combining low on-state resistance with high transconductance. These superior technology die are assembled by state of the art techniques into the TO-240 package, featuring 2.5kV rms isolation and solid M5 screw connections. The small footprint means the package is highly suited to power applications where space is a premium. Available in two versions, IRFK.D... for fast switching and IRFK.F... for oscillation sensitive applications.

$$V_{DS} = 200V$$

$$R_{DS(on)} = 30m\Omega$$

$$I_D = 70A$$

Absolute Maximum Rating

	Parameter	Max.	Units
$I_D @ T_C=25^\circ C$	Continuous Drain Current	70	A
$I_D @ T_C=100^\circ C$	Continuous Drain Current	41	A
I_{DM}	Pulse Drain Current	280	A ①
$P_D @ T_C=25^\circ C$	Maximum Power Dissipation	625	W
V_{GS}	Gate-to-Source Voltage	20	V
V_{INS}	R.M.S. Isolation Voltage, circuit to base	2.5	kV
T_J	Operating Junction Temperature Range	-40 to 150	°C
T_{STG}	Storage Temperature Range	-40 to 150	°C

Thermal and Mechanical Specifications

	Parameter	Min.	Typ.	Max.	Units
R_{thJC}	Junction-to-Case	-	-	0.20	K/W ②
R_{thCS}	Case-to-Sink, smooth & greased surface	-	0.1	-	K/W
T	Mounting Torque +10%				③
	HEXpak to Heatsink	-	5	-	Nm
	Busbar to HEXpak	-	3	-	Nm
wt	Approximate Weight	-	140	-	g
		-	5	-	oz

Notes:

- ① - Repetitive Rating: Pulse width limited by maximum junction temperature see figure 8.
- ② - Per Module.
- ③ - A mounting compound is recommended and the torque should be rechecked after a period of three hours to allow for the spread of the compound.

IRFK3D250, IRFK3F250



Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (Unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions	
$B_{V_{DS}}$	Drain-to-Source Breakdown voltage	200	-	-	V	$V_{GS}=0\text{V}$, $I_D=1.0\text{mA}$	
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	-	24	30	m Ω	$V_{GS}=10\text{V}$, $I_D=41\text{A}$	
$I_{D(on)}$	On-State Drain Current	70	-	-	A	$V_{DS} > I_{D(on)} \times R_{DS(on)}$ max, $V_{GS}=10\text{V}$	
$V_{GS(th)}$	Gate Threshold Voltage	2.0	-	4.0	V	$V_{DS}=V_{GS}$, $I_D=1.0\text{mA}$	
g_{fs}	Forward Transconductance ④	36	54	-	S	$V_{DS} > 50\text{V}$, $I_D=41\text{A}$	
I_{DSS}	Zero Gate Voltage Drain Current	-	-	0.75	mA	$V_{DS}=V_{DSmax}$, $V_{GS}=0\text{V}$	
		-	-	3.0	mA	$V_{GS}=10\text{V}$, $T_C=125^\circ\text{C}$, $V_{DS}=V_{DSmax} \times 0.8$	
I_{GSS}	Gate-to-Source Leakage Forward	-	-	300	nA	$V_{GS}=20\text{V}$	
I_{GSS}	Gate-to-Source Leakage Reverse	-	-	-300	nA	$V_{GS}=20\text{V}$	
Q_g	Total Gate Charge	-	260	390	nC	$I_D=70\text{A}$, $V_{GS}=10\text{V}$,	
Q_{gs}	Gate-to-Source Charge	-	48	72	nC	$V_{DS}=V_{DSmax} \times 0.8$	
Q_{gd}	Gate-to-Drain ("Miller") Charge	-	138	210	nC		
$t_{d(on)}$	Turn-on Delay Time	IRFK3D250	-	40	-	ns	$V_{DD}=95\text{V}$, $I_D=41\text{A}$,
		IRFK3F250	-	45	-	ns	
t_r	Rise Time	IRFK3D250	-	100	-	ns	$V_{GS}=10\text{V}$,
		IRFK3F250	-	125	-	ns	
$t_{d(off)}$	Turn-off Delay Time	IRFK3D250	-	160	-	ns	$R_{SOURCE}=3.3\Omega$
		IRFK3F250	-	210	-	ns	
t_f	Fall Time	IRFK3D250	-	50	-	ns	
		IRFK3F250	-	80	-	ns	
L_{DS}	Drain-to-Source Inductance	-	18	-	nH		
C_{iss}	Input Capacitance	-	9.0	-	nF	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$,	
C_{oss}	Output Capacitance	-	2.5	-	nF	$f=1.0\text{MHz}$	
C_{res}	Reverse Transfer Capacitance	-	0.7	-	nF		
	Linear Derating Factor	-	-	5	W/K		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	-	-	70	A	
I_{SM}	Pulsed Source Current (Body Diode)	-	-	245	A	
V_{SD}	Diode Forward Voltage	-	-	2.0	V	$V_{GS}=0\text{V}$, $I_S=70\text{A}$, $T_C=25^\circ\text{C}$
t_{rr}	Reverse Recovery Time	9160	320	640	ns	$di/dt=400\text{A}/\mu\text{s}$, $T_J=150^\circ\text{C}$
Q_{rr}	Reverse Recovered Charge	6.6	13.0	26.0	μC	$I_S=70\text{A}$

Notes:

④ - Pulse Width $\leq 300\mu\text{s}$; Duty cycle $\leq 2\%$.



IRFK3D250, IRFK3F250

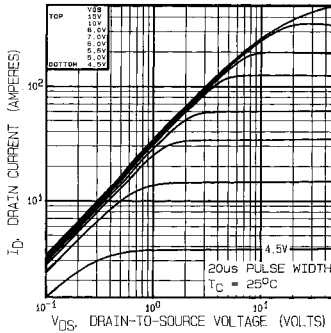


Fig 1. Typical Output Characteristics, $T_C = 25^\circ\text{C}$

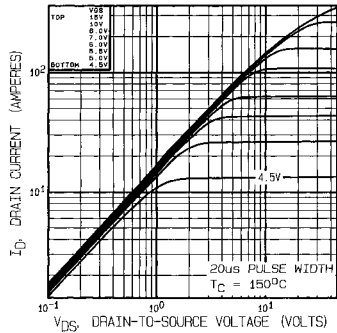


Fig 2. Typical Output Characteristics, $T_C = 150^\circ\text{C}$

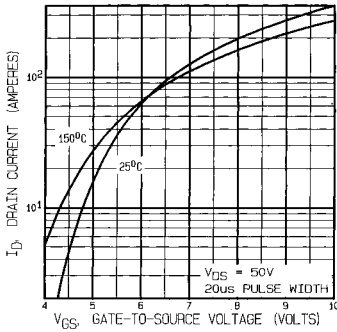


Fig 3. Typical Transfer Characteristics

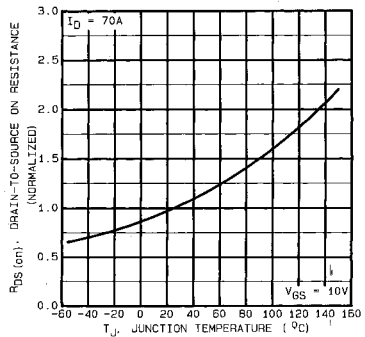


Fig 4. Normalized On-Resistance Vs. Temperature

IRFK3D250, IRFK3F250

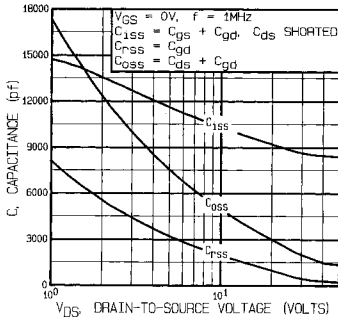


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

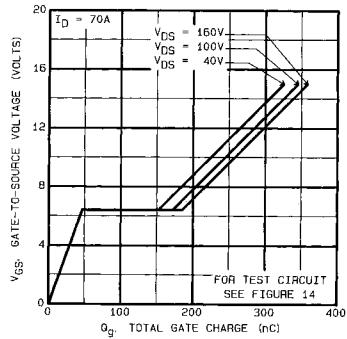


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

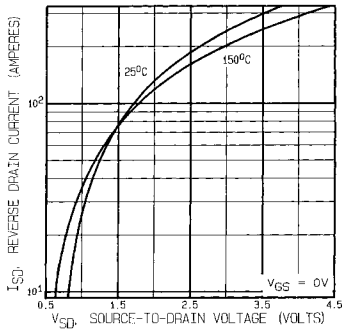


Fig 7. Typical Source-Drain Diode Forward Voltage

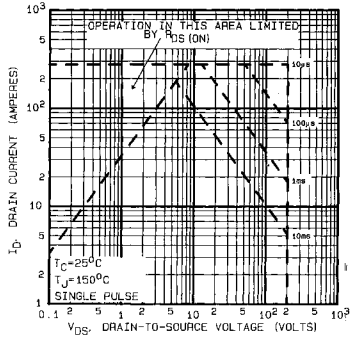


Fig 8. Maximum Safe Operating Area

IRFK3D250, IRFK3F250

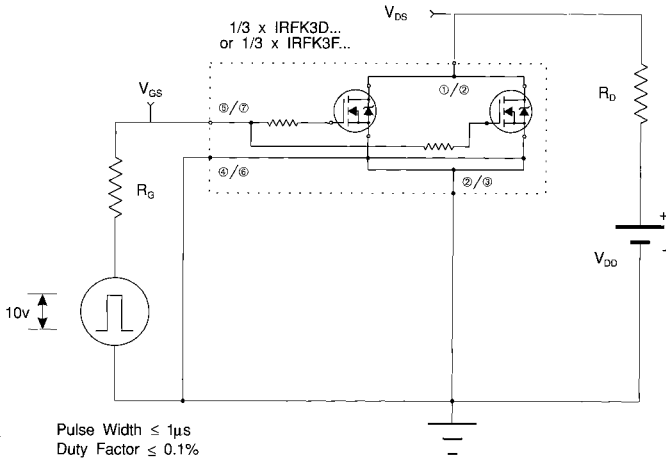


Fig 11a. Switching Time Test Circuit

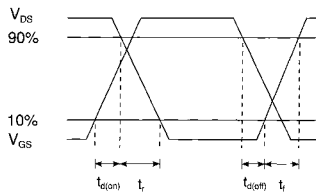


Fig 11b. Switching Time Waveforms



IRFK3D250, IRFK3F250

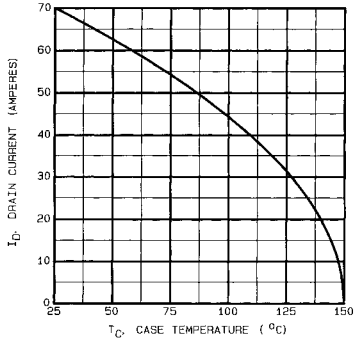


Fig 9. Maximum Drain Current Vs. Case Temperature

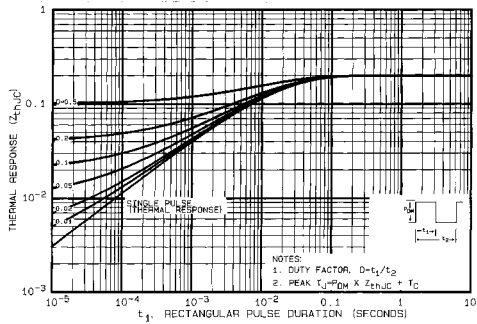
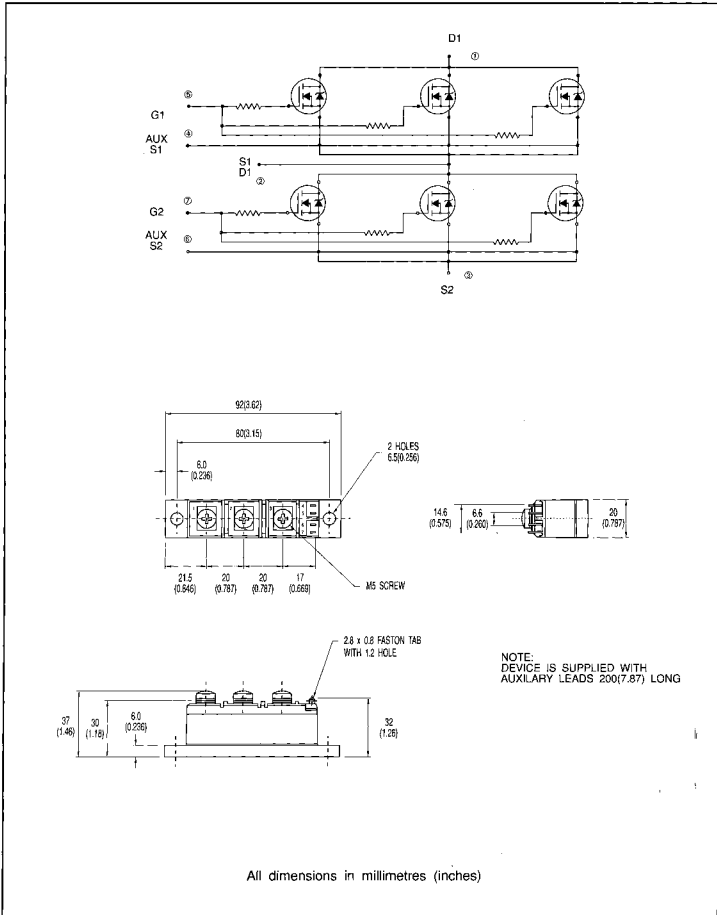


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Case



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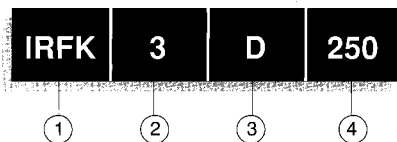
Circuit Configuration and Outline



IRFK3D250,IRFK3F250



Part Numbering



1. - HEX-pak Module.
2. - Number of arms of bridge.
3. - D - Fast switching.
- F - Oscillation resistant for sensitive applications.
4. - Voltage code:-
 - 054 - 60V
 - 150 - 100V
 - 250 - 200V
 - 350 - 400V
 - 450 - 500V
 - C50 - 600V

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